HALOGEN

FREE

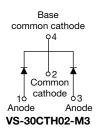


www.vishay.com

Vishay Semiconductors

Hyperfast Rectifier, 2 x 15 FRED Pt®





| PRIMARY CHARACTERISTICS | | | | | | | | | |
|----------------------------------|--------------------|--|--|--|--|--|--|--|--|
| V_{R} | 200 V | | | | | | | | |
| V _F at I _F | 0.78 V | | | | | | | | |
| t _{rr} typ. | See Recovery table | | | | | | | | |
| T _J max. | 175 °C | | | | | | | | |
| I _{F(AV)} | 2 x 15 A | | | | | | | | |
| Package | TO-220AB 3L | | | | | | | | |
| Circuit configuration | Common cathode | | | | | | | | |

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | | | |
|------------------------------------|-----------------------------------|------------------------|-------------------------|--------|-------|--|--|--|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | |
| Peak repetitive reverse voltage | | V_{RRM} | | 200 | V | | | | |
| Average rectified forward current | per diode | I _{F(AV)} | T _C = 159 °C | 15 | | | | | |
| | per device | | | 30 | Α | | | | |
| Non-repetitive peak surge current | I _{FSM} | T _J = 25 °C | 200 | | | | | | |
| Operating junction and storage ter | T _J , T _{Stg} | | -65 to +175 | °C | | | | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | | | | |
|--|-------------------------------------|--|---------|------|------|-------|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | | | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | Ι _R = 100 μΑ | 200 | - | - | | | | | |
| Forward voltage | V _F | I _F = 15 A | - | 0.92 | 1.05 | V | | | | |
| | | I _F = 15 A, T _J = 125 °C | - | 0.78 | 0.85 | | | | | |
| Povoros laskago surrent | I _R | $V_R = V_R$ rated | - | - | 10 | μA | | | | |
| Reverse leakage current | | $T_J = 125$ °C, $V_R = V_R$ rated | - 5 300 | | | | | | | |
| Junction capacitance | C _T | V _R = 200 V | - | 57 | - | pF | | | | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8 | - | nH | | | | |



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| DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified) | | | | | | | | | | |
|---|------------------|-----------------------------------|--|------|------|------|-------|--|--|--|
| PARAMETER | SYMBOL | TEST CO | NDITIONS | MIN. | TYP. | MAX. | UNITS | | | |
| | | $I_F = 1 \text{ A}, dI_F/dt = 50$ | - | - | 35 | | | | | |
| Poveree receivery time | t _{rr} | $I_F = 1 A, dI_F/dt = 100$ | - | - | 30 | ns | | | | |
| Reverse recovery time | | T _J = 25 °C | | - | 26 | - | ns | | | |
| | | T _J = 125 °C | $I_F = 15 \text{ A}$ | = | 40 | - | | | | |
| Dook receivery current | I _{RRM} | T _J = 25 °C | dl _F /dt = 200 A/μs V _B = 160 V | - | 2.8 | - | Α | | | |
| Peak recovery current | | T _J = 125 °C | 11 | - | 6.0 | - | | | | |
| Reverse recovery charge | Q _{rr} | T _J = 25 °C | | - | 37 | - | nC | | | |
| | | T _J = 125 °C | - | 120 | - | IIC | | | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | | | |
|---|-----------------------------------|--|---------|---|-----|------|--|--|--|--|
| PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS | | | | | | | | | | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C | | | | |
| Thermal resistance, junction-to-case per diode | R _{thJC} | Mounting surface, flat, smooth and greased | - | - | 1.1 | °C/W | | | | |
| Marking device | | Case style TO-220AB 3L | 30CTH02 | | | | | | | |

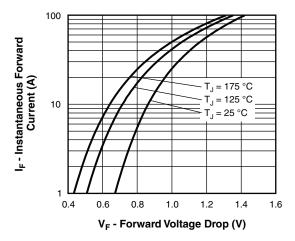


Fig. 1 - Typical Forward Voltage Drop Characteristics

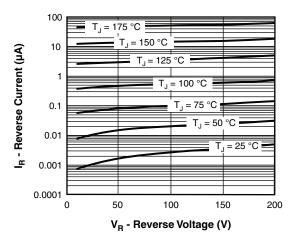


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

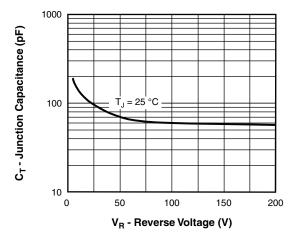


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

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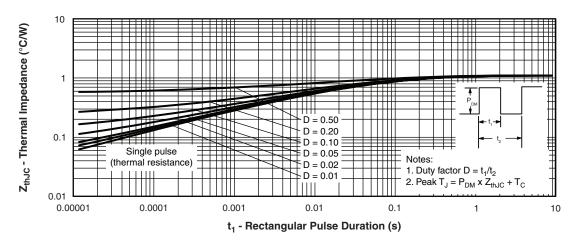


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

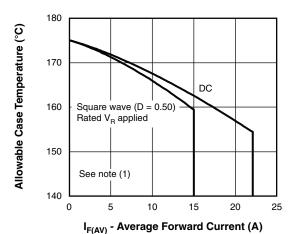


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

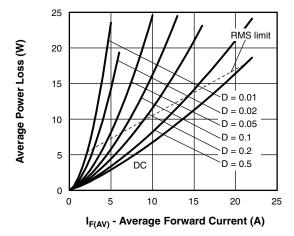


Fig. 6 - Forward Power Loss Characteristics

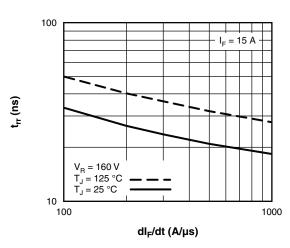


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

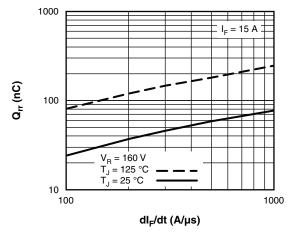
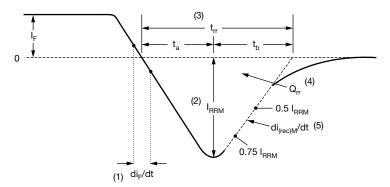


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

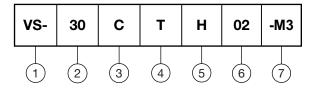
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating (30 = 30 A)
- 3 C = common cathode
- **4** T = TO-220
- H = hyperfast recovery
- 6 Voltage rating (02 = 200 V)
- 7 Environmental digit:
 - -M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | | | | |
|---|----|--------------------------|--|--|--|--|--|--|
| PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION | | | | | | | | |
| VS-30CTH02-M3 | 50 | Antistatic plastic tubes | | | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | | | |
|--|--------------------------|--|--|--|--|--|--|
| Dimensions <u>www.vishay.com/doc?96154</u> | | | | | | | |
| Part marking information | www.vishay.com/doc?95028 | | | | | | |



Vishay Semiconductors

TO-220AB 3L

DIMENSIONS in millimeters and inches





Conforms to JEDEC® outline TO-220AB

| SYMBOL | MILLIM | MILLIMETERS | | INCHES | | NOTES | SYMBOL | MILLIMETERS | | INCHES | | NOTES |
|--------|--------|-------------|-------|--------|-------|-------|----------|-------------|-------|--------|-------|-------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES | NOTES | STIVIBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| Α | 4.25 | 4.65 | 0.167 | 0.183 | | | D2 | 11.68 | 13.30 | 0.460 | 0.524 | 6, 7 |
| A1 | 1.14 | 1.40 | 0.045 | 0.055 | | | Е | 10.11 | 10.51 | 0.398 | 0.414 | 3, 6 |
| A2 | 2.50 | 2.92 | 0.098 | 0.115 | | | E1 | 6.86 | 8.89 | 0.270 | 0.350 | 6 |
| b | 0.69 | 1.01 | 0.027 | 0.040 | | | е | 2.41 | 2.67 | 0.095 | 0.105 | |
| b1 | 0.38 | 0.97 | 0.015 | 0.038 | 4 | | e1 | 4.88 | 5.28 | 0.192 | 0.208 | |
| b2 | 1.20 | 1.73 | 0.047 | 0.068 | | | H1 | 6.09 | 6.48 | 0.240 | 0.255 | 6 |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | L | 13.52 | 14.02 | 0.532 | 0.552 | |
| С | 0.36 | 0.61 | 0.014 | 0.024 | | | L1 | 3.32 | 3.82 | 0.131 | 0.150 | 2 |
| c1 | 0.36 | 0.56 | 0.014 | 0.022 | 4 | | ØΡ | 3.54 | 3.91 | 0.139 | 0.154 | |
| D | 14.85 | 15.35 | 0.585 | 0.604 | 3 | | Q | 2.60 | 3.00 | 0.102 | 0.118 | |
| D1 | 8.38 | 9.02 | 0.330 | 0.355 | | | | | | | | |

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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